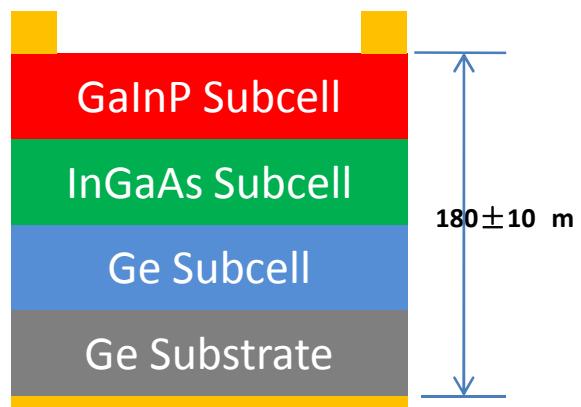


- High conversion efficiency and long life time
- 100% chip sorting and testing
- Long time reliability test and outdoor running test
- Capability of design cell structure and electrode pattern according to customer

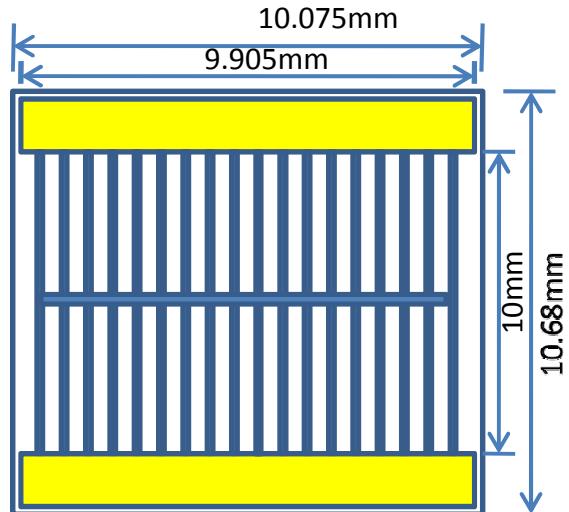
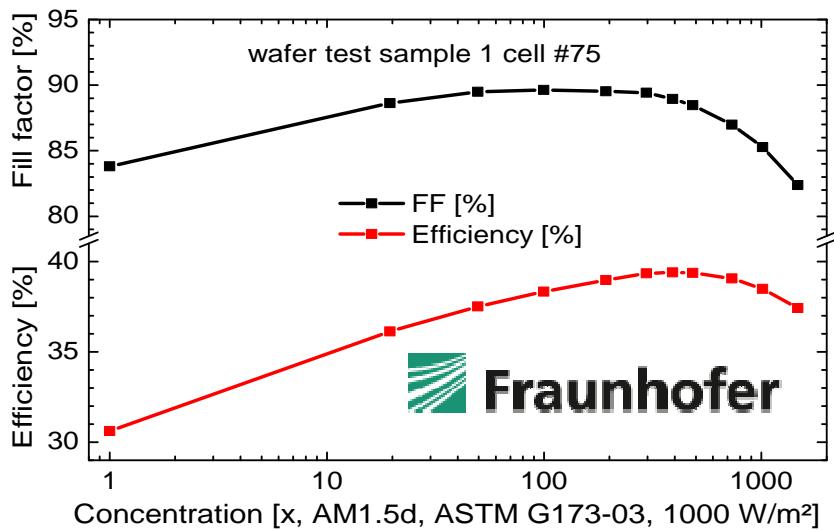
Material	GalnP/InGaAs/Ge	I-V curves under 1000X concentration	
AR	TiO ₂ /Al ₂ O ₃	I _{sc}	12.8～14.2A
Size	10.68mm×10.075mm±0.1	V _{oc}	3.15～3.30V
Area	99mm ²	FF	80%～90%
Conductivity	N on P	Efficiency	36%～40%

➤ **1000X Thermal coefficient**

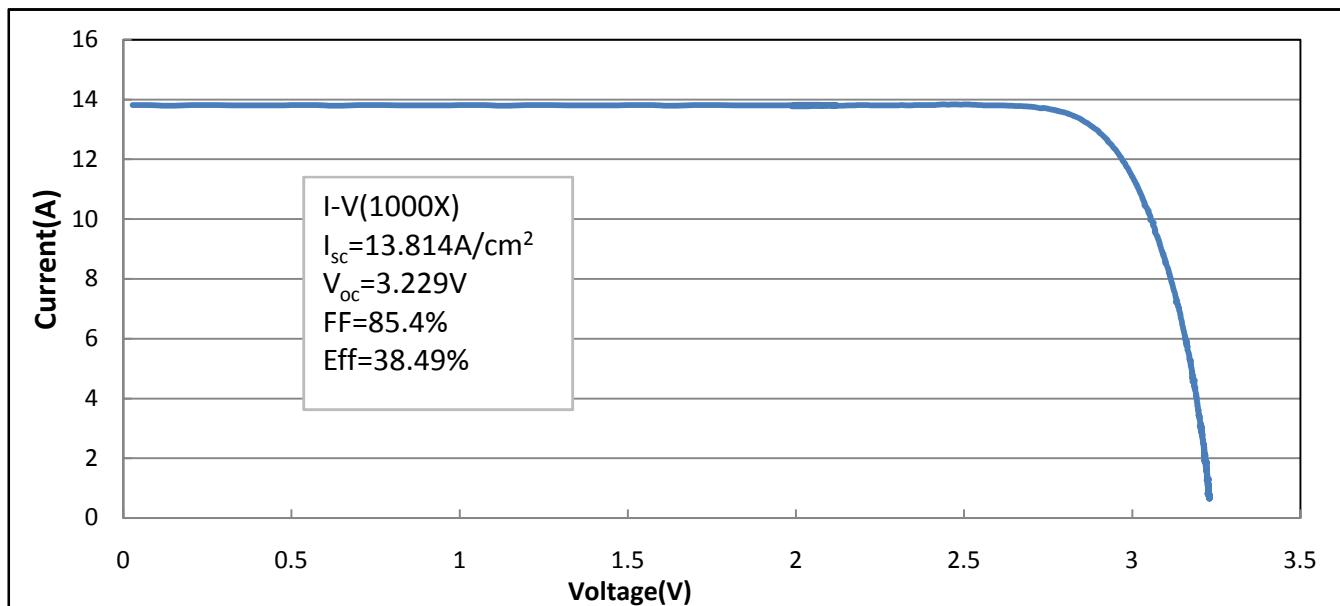
△I _{sc}	+0.09%/°C
△V _{oc}	-0.15%/°C
△P _{max}	-0.14%/°C
△FF	-0.07%/°C



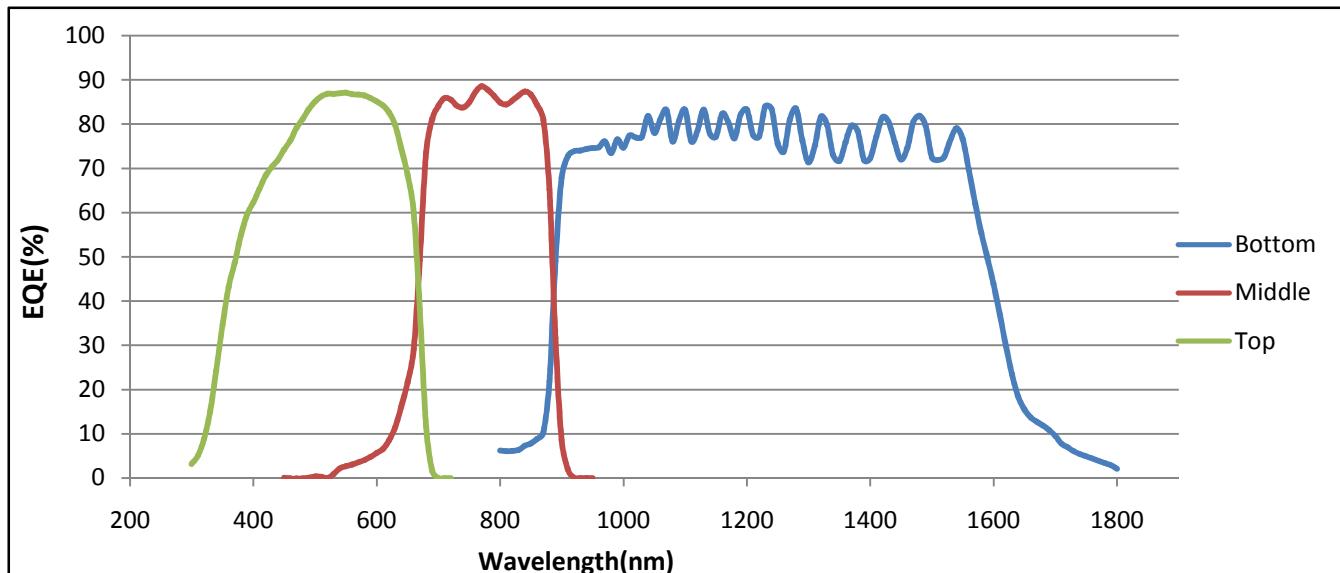
➤ **Efficiency and Fill factor Vs. concentration**



➤ I-V curves under 1000X concentration



➤ EQE measurement results



➤ Reliability test (IEC 62108)

Test items	Test conditions	Quantity	Requirement
Damp heat	85 °C, 85% RH, 1000h	15	NPmp > 0.92
Thermal cycling	500cycles, -40 °C to +110 °C	15	NPmp > 0.92